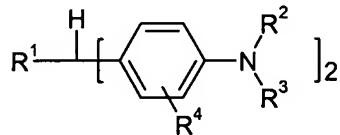


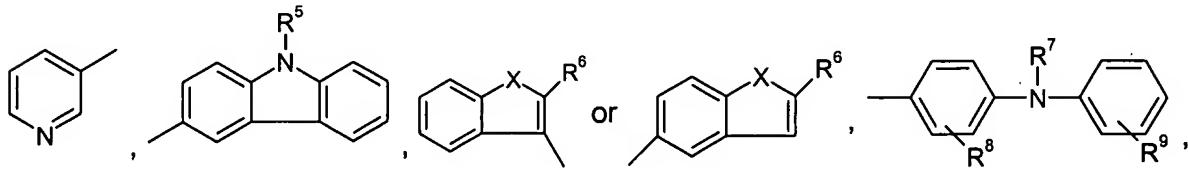
In the Claims

1. (currently amended) A process for preparing a dry film resist, which process comprises forming a photocurable resin composition onto a support film with a thickness of 1 to 50 µm and optionally laminate a protective film onto the photocurable composition layer to obtain a dry film resist; whereby the photocurable resin is formed from a homogeneous mixture comprising
 - (a) from 20-90wt% of an alkaline soluble binder oligomer or acrylic polymer having carboxylic acid function as a pendant group and having a molecular weight of about 2,000 to 2,000,000, and an acid value from 50 to 600 mg KOH/g;
 - (b) from 5 to 60wt% of one or more photopolymerizable monomers which are compatible with the oligomers and polymers of component (a);
 - (c) from 0.01 to 20% by weight of one or more photoinitiators;
 - (d) from 0 to 20% by weight of additives and/or assistants; and
 - (e) from 0.1 to 10 % by weight of a leuco triphenylmethane dye of the formula I



wherein

R^1 is a residue selected from



R^2 is C_1 - C_{12} alkyl or phenyl which may be mono-, di- or tri-substituted by C_1 - C_6 alkyl, trifluoromethyl, C_{1-6} alkoxy, C_{1-6} alkylthio, halogen and nitro;

R^3 is hydrogen or C₁-C₁₂ alkyl;

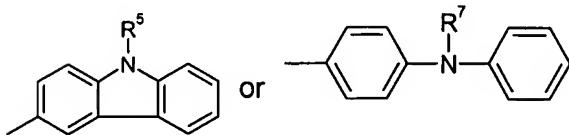
R^4 to R^9 independently of one another are hydrogen or C_1 - C_{12} alkyl; and

X is O, S, NH or N-C₁-C₁₂-alkyl;

where the total of (a) through (e) equals being 100% by weight.

2. (previously presented) A process according to claim 1, wherein in formula I

R^1 is a residue



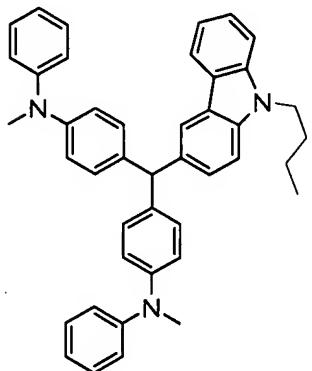
R^2 is unsubstituted phenyl,

R^3 is C_1 - C_4 alkyl

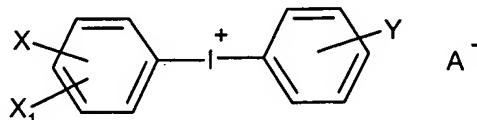
R^4 is hydrogen; and

R^5 and R^7 are C_1 - C_4 alkyl.

3. (previously presented) A process according to claim 1, wherein the leuco triphenylmethan dye is 4,4'-(9-Butyl-9H-carbazol-3-yl)methylene]bis[N-methyl-N-phenylaniline of the formula



4. (previously presented) A process according to claim 1, wherein component d) includes a diaryliodonium of formula



wherein

X is branched C_3 - C_{20} alkyl or C_3 - C_8 cycloalkyl;

X_1 is hydrogen, linear C_1 - C_{20} alkyl, branched C_3 - C_{20} alkyl or C_3 - C_8 cycloalkyl; with the proviso that the sum of the carbon atoms in X and X_1 is at least 4;

Y is linear C_1 - C_{10} alkyl, branched C_3 - C_{10} alkyl or C_3 - C_8 cycloalkyl;

A^- is a non-nucleophilic anion, selected from the group consisting of $(BF_4)^-$, $(SbF_6)^-$, $(PF_6)^-$, $(B(C_6F_5)_4)^-$, C_1-C_{20} alkylsulfonate, C_2-C_{20} haloalkylsulfonate, unsubstituted C_6-C_{10} arylsulfonate, camphor-sulfonate, C_1-C_{20} -perfluoroalkylsulfonylmethide, C_1-C_{20} -perfluoroalkylsulfonylimide, and C_6-C_{10} arylsulfonate substituted by halogen, NO_2 , C_1-C_{12} alkyl, C_1-C_{12} halo-alkyl, C_1-C_{12} alkoxy or by $COOR_1$; and

R_1 is C_1-C_{20} alkyl, phenyl, benzyl; or phenyl mono- or poly-substituted by C_1-C_{12} alkyl, C_1-C_{12} alkoxy or by halogen.

5. (previously presented) A dry film resist obtained by a process according to claim 1.

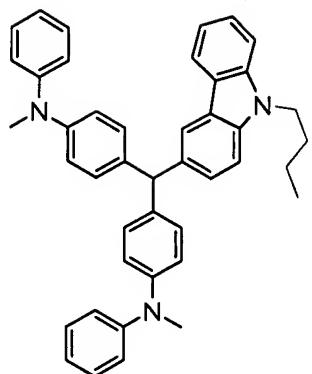
6. (previously presented) A process for preparing a dry film resist element comprising the steps of

- (A) forming a photocurable resin composition layer made of ingredients (a)-(e) according to claim 1 onto a support film with a thickness of 1 to 50 μm , and laminate a protective film onto the photocurable composition layer to obtain a dry film resist;
- (B) removing the protective film before use, and thermally laminate the photocurable composition layer onto the surface of a desired substrate for the application of the dry film resist at 100-150°C;
- (C) exposure to radiation through a mask or by direct laser irradiation; and
- (D) removing the support film and wash away the unexposed (uncured) area by development.

7. (previously presented) A dry film resist element obtained by a process according to claim 6.

8. (canceled)

9. (previously presented) A process according to claim 6 wherein component (e) is 4,4'-(9-butyl-9H-carbazol-3-yl)methylene]bis[N-methyl-N-phenylaniline of the formula



10. (previously presented) A process according to claim 6 for forming copper circuit pattern of printed circuit board, LSI packaging etching resist or plating resist, for solder resist or for forming cell or electrode pattern in flat display panel applications.